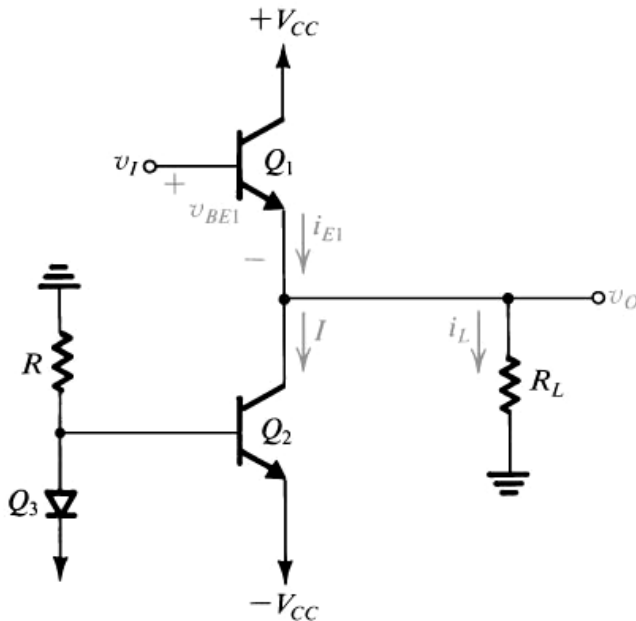


# OUTPUT STAGES

Example:

(P14.3)

Design the circuit below using a  $+9V$  supply to provide a design capable of  $\pm 7V$  outputs with a  $1k\Omega$  load. Use the smallest possible total supply current.

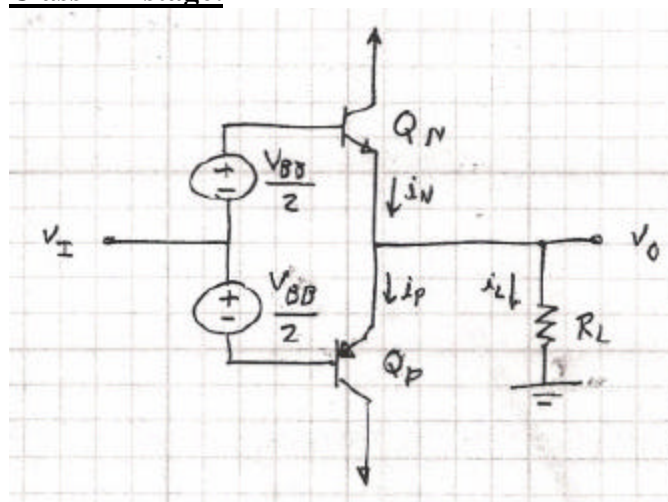


Example #2:

(D14.14)

A class B output stage is required to deliver an average power of  $100W$  into a  $16\Omega$  load. The power supply should be  $4V$  greater than the corresponding peak sine-wave output voltage. Determine the power-supply voltage required (to the nearest volt), the peak current from each supply, the total supply power, and the power-conversion efficiency.

## Class AB stage:



- This type of stage uses both the “A” and the “B” to produce a “push-pull” operation without the deadband.

# OUTPUT STAGES

- The voltage offset at the input crossover distortion

$$I_Q = I_S e^{\frac{V_{BE}}{2V_T}} \Rightarrow V_{BE} = 2V_T \ln \frac{I_Q}{I_S}$$

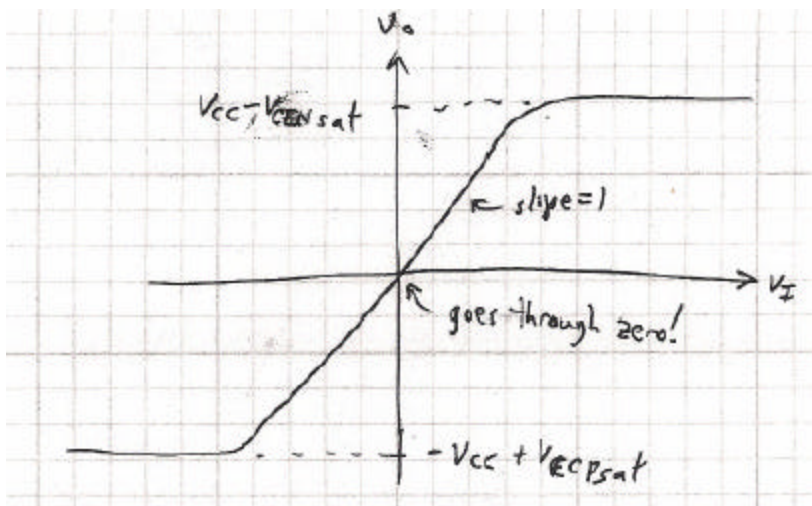
$$i_N = I_S e^{\frac{V_{BE_N}}{V_T}} \Rightarrow V_{BE_N} = V_T \ln \frac{i_N}{I_S}$$

$$i_P = I_S e^{\frac{V_{BE_P}}{V_T}} \Rightarrow V_{BE_P} = V_T \ln \frac{i_P}{I_S}$$

$$V_{BE_N} + V_{BE_P} = V_{BE}$$

$$\Rightarrow V_T \ln \left( \frac{i_N}{I_S} \right) + V_T \ln \left( \frac{i_P}{I_S} \right) = 2V_T \ln \frac{I_Q}{I_S}$$

$$\Rightarrow i_N i_P = I_Q^2 \quad \leftarrow \text{smooth transition at } v_o = 0 \text{ from } Q_N \text{ to } Q_P \text{ conducting}$$



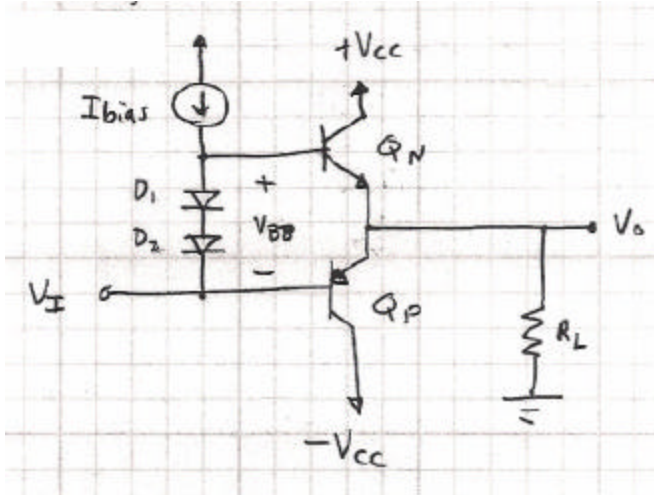
## Output resistance:

- This will change as  $V_o$  changes  $\Rightarrow$  Therefore, only find for a fixed value of  $V_o$ .

# OUTPUT STAGES

Biasing Class AB stage:

- Biasing with diodes:



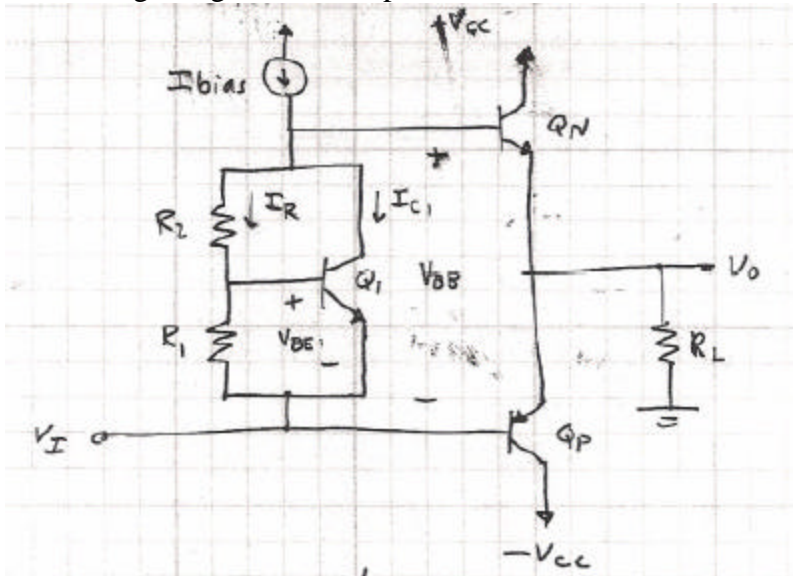
- If output transistor emitter area is  $n$  times larger than diode junction area, then

$$i_N = I_S e^{\frac{V_{BE_N}}{V_T}} \quad i_P = I_S e^{\frac{V_{BE_P}}{V_T}}$$

$$i_{\text{diode}} = \frac{I_S}{n} e^{\frac{V_{\text{Diode}}}{V_T}}$$

$$I_Q = n I_{\text{bias}}$$

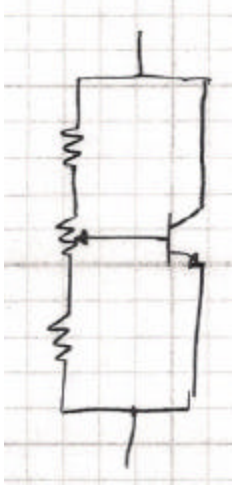
- Biasing using a  $V_{BE}$  multiplier



# OUTPUT STAGES

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$V_{BB}$  can be set using resistors adjusted to get the right  $I_Q$ :



## Thermal Runaway in BJT's:

- As Temperature  $\uparrow$  by  $1^\circ\text{C}$ :
  - If collector current is fixed,  $V_{BE}$  drops by  $2\text{mV}$  { $V_{BE}$  dependence  $\Rightarrow -2\text{mV}/^\circ\text{C}$ }
  - If  $V_{BE}$  is fixed, collector current increases 8%
- As collector current  $\uparrow$ , BJT Temp  $\uparrow$  which causes collector current  $\uparrow$ , ...  
THERMAL RUNAWAY
- Solution is to :
  - Place D1, D2 or Q1 in \_\_\_\_\_
  - IC Design  $\Rightarrow$  place them \_\_\_\_\_
  - In discrete design  $\Rightarrow$  mount D1, D2, or Q1 on the \_\_\_\_\_